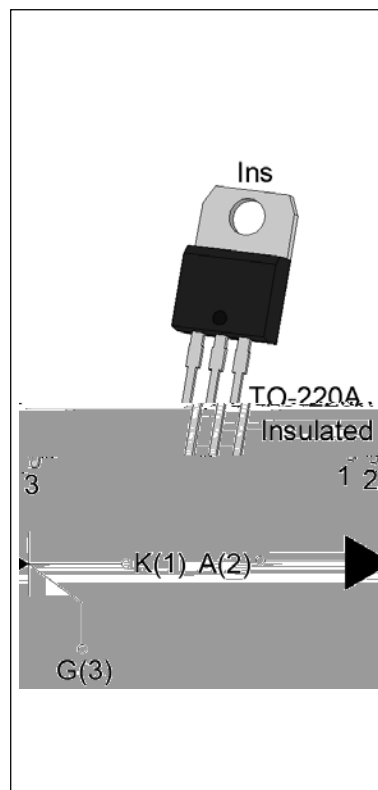




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1230A SCR provides high dv/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1230A provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906).

Package TO-220A is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM}/V_{RRM}	1200	V
I_{GT}	≤ 40	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
Average on-state current ($T_c = 50^\circ\text{C}$)	$I_{T(AV)}$	19	A
RMS on-state current ($T_c = 50^\circ\text{C}$)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	370	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		400	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	685	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	200	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	-	40	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=125 R_L=3.3K\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=1A$	-	-	100	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$	1500	-	-	V/ μs
t_{on}	$I_G=100mA I_A=1A I_R=100mA$ $T_j=25$	-	5	-	μs
t_{off}		-	70	-	

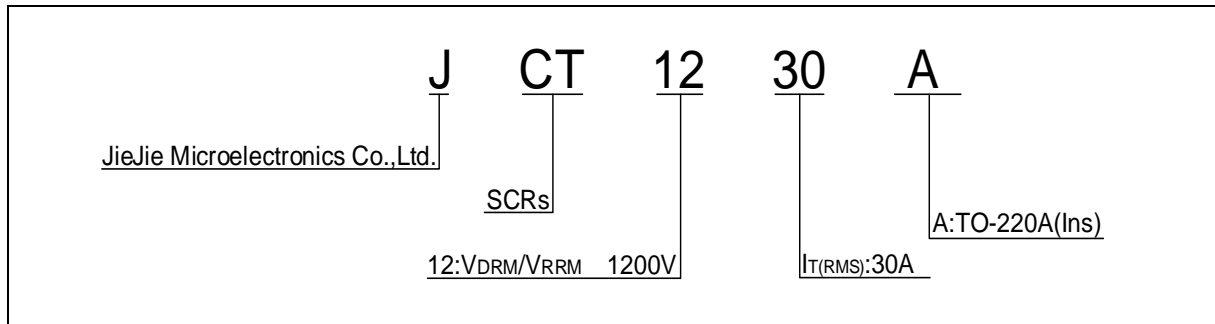
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=60A t_p=380\mu s$	$T_j=25$	1.55	V
V_{TO}	Threshold voltage	$T_j=125$	0.76	V
R_D	Dynamic resistance	$T_j=125$	15	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	8	μA
I_{RRM}		$T_j=125$	3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value aP < (i.67 0t-0.00.48 re f4
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ORDERING INFORMATION



MARKING

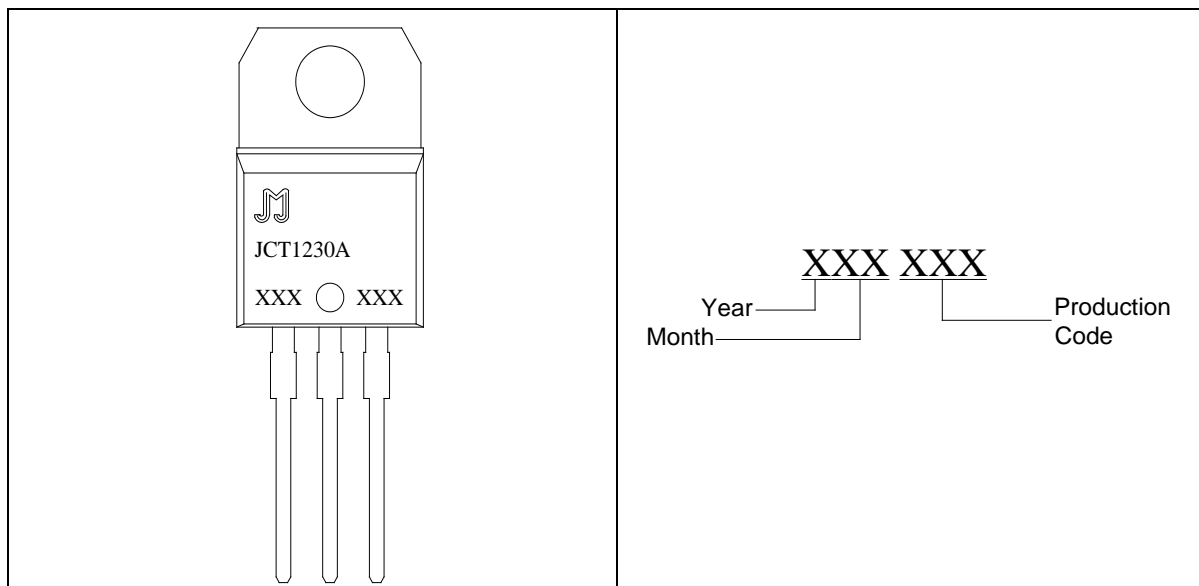
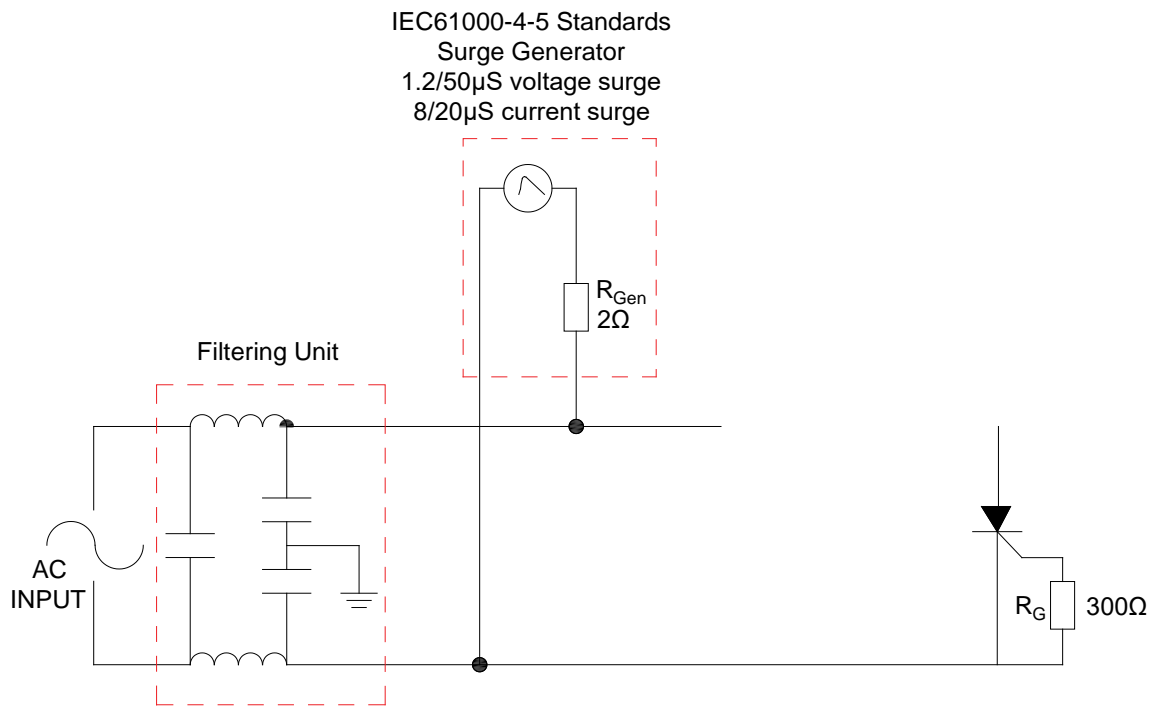


FIG.1 Maximum power dissipation versus
RMS on-state current

FIG.2: RMS on-state current versus case
temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



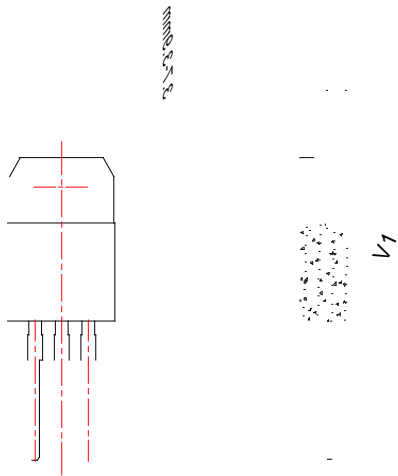
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1230A	1200	40	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



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